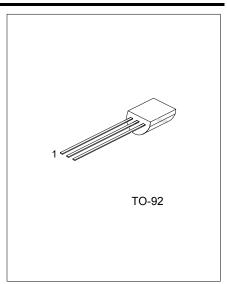
# UNISONIC TECHNOLOGIES CO., LTD

2N7000 Power MOSFET

# N-CHANNEL ENHANCEMENT MODE

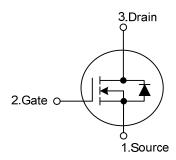
#### **■** DESCRIPTION

The UTC **2N7000** has been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. It can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. The product is particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications



#### **■ FEATURES**

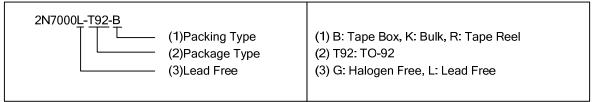
#### ■ SYMBOL



## **■ ORDERING INFORMATION**

Ordering Number		Dookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
2N7000L-T92-B	2N7000G-T92-B	TO-92	S	G	D	Tape Box	
2N7000L-T92-K	2N7000G-T92-K	TO-92	S	G	D	Bulk	
2N7000L-T92-R	2N7000G-T92-R	TO-92	S	G	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



<sup>\*</sup>High density cell design for low R<sub>DS(ON)</sub>

<sup>\*</sup>Voltage controlled small signal switch

<sup>\*</sup>Rugged and reliable

<sup>\*</sup>High saturation current capability

2N7000 Power MOSFET

## ■ ABSOLUTE MAXIMUM RATINGS ( Ta=25°C )

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	60	V
Drain-Gate Voltage (R <sub>GS</sub> ≤1MΩ)		$V_{DGR}$	60	V
Gate -Source Voltage	Continuous	V <sub>GS</sub>	±20	V
	Non Repetitive (tp<50μs)		±40	V
Maximum Drain Current Continuous		l <sub>o</sub>	115	mA
Maximum Brain Current	Pulsed	ID	800	mA
Maximum Power Dissipation		P <sub>D</sub>	400	mW
Derated above 25°C		FD	3.2	mW/°C
Operating and Storage Temperature		$T_{J,}T_{STG}$	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## **■ THERMAL DATA**

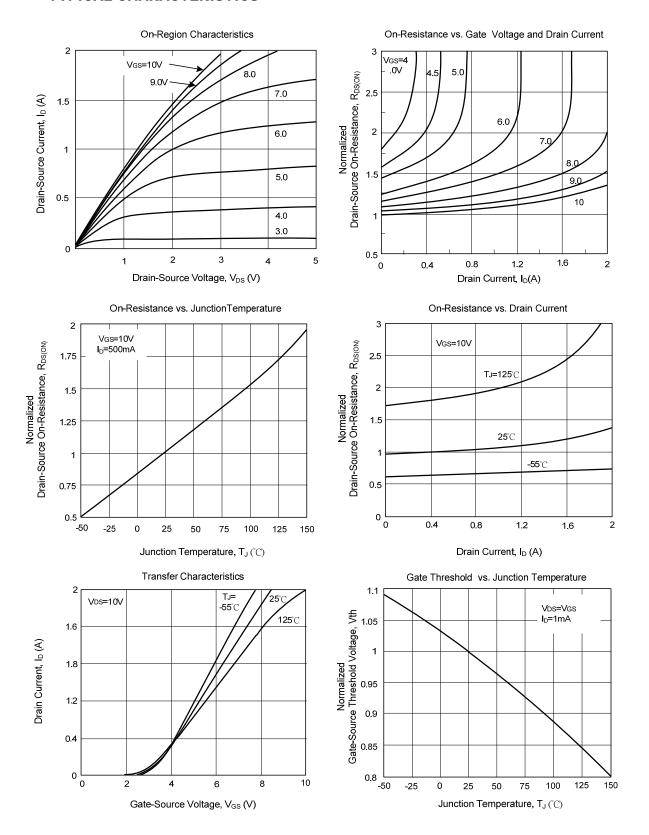
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	312.5	°C/W

## ■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0 $V$ , $I_D$ =10 $\mu$ A	60			V	
Drain Source Leakage Current		V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μΑ	
Drain-Source Leakage Current	I <sub>DSS</sub>	T <sub>J</sub> =125°C			0.5	mA	
Gate-Body leakage, Forward	I <sub>GSSF</sub>	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V			100	nA	
Gate-Body leakage Reverse	I <sub>GSSR</sub>	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100	nA	
ON CHARACTERISTICS (Note)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	2.1	2.5	V	
	В	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA		1.2	7.5		
Static Drain-Source On-Resistance		T <sub>J</sub> =100°C		1.7	13.5	Ω	
Static Dialii-Source Off-Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =5.0V, $I_D$ =50mA		1.7	7.5	52	
		T <sub>J</sub> =100°C 2.4					
Drain-Source On-Voltage	V <sub>DS(ON)</sub>	$V_{GS}$ = 10V, $I_{D}$ =500mA		0.6	3.75	V	
	V DS(ON)	$V_{GS} = 5.0V, I_D = 50mA$		0.09	1.5	1	
On-State Drain Current	$I_{D(ON)}$	$V_{GS}$ =10V, $V_{DS} \ge 2V_{DS(ON)}$	500	2700		mA	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C <sub>ISS</sub>			20	50	pF	
Output Capacitance	Coss	$V_{DS}$ =25V, $V_{GS}$ =0V, f=1.0MHz		11	25	pF	
Reverse Transfer Capacitance	C <sub>RSS</sub>			4	5	pF	
Turn-On Time	ton	$V_{DD}$ =30V, $R_L$ =150 $\Omega$ ,			20	no	
Turn-On Time		$I_D$ =200mA, $V_{GS}$ =10V, $R_{GEN}$ =25 $\Omega$			20	ns	
Turn-Off Time	4	$V_{DD}$ =30V, $R_L$ =150 $\Omega$ , $I_D$ =200mA,			20	ns	
Turi-On Time	t <sub>OFF</sub>	$V_{GS}$ =10V, $R_{GEN}$ =25 $\Omega$			20	113	
DRAIN-SOURCE DIODE CHARACT	ERISTICS A	AND MAXIMUM RATINGS					
Drain-Source Diode Forward	$V_{SD}$	V <sub>GS</sub> =0V, Is=115mA(Note )		0.88	1.5	V	
Voltage	VSD	VGS-UV, IS-TIBITIA(INUTE)		0.00	1.5	v	
Maximum Continuous Drain-Source	Is				115	mA	
Diode Forward Current	15		<u> </u>		113	111/4	
Maximum Pulsed Drain-Source	I <sub>SM</sub>				0.8	Α	
Diode Forward Current	ioivi				0.0		

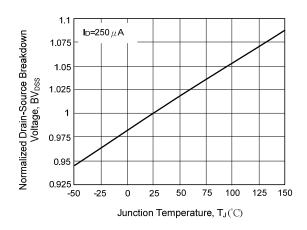
Note: Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%

## ■ TYPICAL CHARACTERISTICS

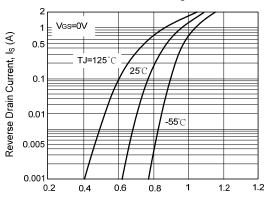


## **■ TYPICAL CHARACTERISTICS(Cont.)**

Breakdown Voltage vs. Junction Temperature

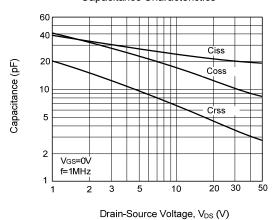


Reverse Drain Current vs. Body Diode Forward Voltage

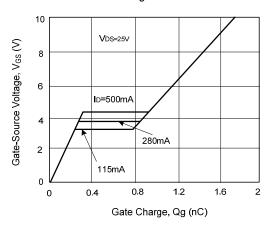


Body Diode Forward Voltage, V<sub>SD</sub> (V)

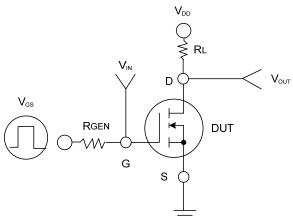
Capacitance Characteristics

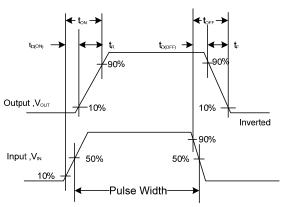


Gate Charge Characteristics

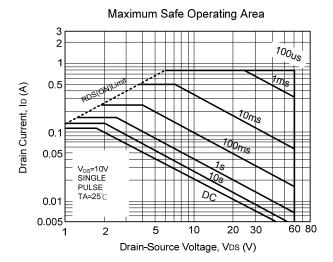


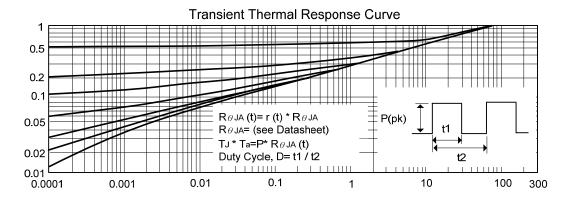
Switching Waveforms





## **■ TYPICAL CHARACTERISTICS(Cont.)**





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